

AMENDMENTS TO THE CLAIMS:

LISTING OF CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-5 (canceled).

Claim 6 (currently amended): The semiconductor device as claimed in claim ~~[[2]]~~ 18, wherein the noise reduction condenser of said condenser chip is formed by a MOS capacity.

Claims 7-8 (canceled).

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Claim 9 (currently amended): A semiconductor device comprising: a first semiconductor chip having a circuit block, a power supply line and a ground line; and a second semiconductor chip stacked on said first semiconductor chip, wherein said first semiconductor chip has ~~[[a]]~~ at least one first electrode pad separated from a circuit formed within said first semiconductor chip;

said second semiconductor chip has ~~a second~~ at least one first electrode pad separated from a circuit formed within said second semiconductor chip; and

an inductor connected to at least one of said power line and said ground line is formed by connecting said at least one first electrode pad of said first semiconductor chip and said ~~second~~ at least one first electrode pad of said second semiconductor chip by a bonding wire.

Claim 10 (currently amended): The semiconductor device as claimed in claim 9, wherein a plurality of said first electrode pads of said first semiconductor chip are provided and a plurality of said ~~second~~ first electrode pads of said second semiconductor chip are provided; and

said inductor is formed by alternately and sequentially connecting said first electrode pads of said first semiconductor chip and said ~~second~~ first electrode pads of said second semiconductor chip by bonding wires.

Claims 11-12 (canceled).

Claim 13 (currently amended): The semiconductor device as claimed in claim [[3]] 19, wherein the noise reduction condenser of said condenser chip is formed by a MOS capacity.

Claim 14 (currently amended): The semiconductor device as claimed in claim [[4]] 20, wherein the noise reduction condenser of said condenser chip is formed by a MOS capacity.

Claim 15 (currently amended): The semiconductor device as claimed in claim [[5]] 21, wherein the noise reduction condenser of said condenser of said condenser chip is formed by a MOS capacity.

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Claims 16-17 (canceled).

Claim 18 (new): A semiconductor device comprising:

a semiconductor chip having a plurality of circuit blocks, a power supply line and a ground line, said power supply line and said ground line being connected to each of said plurality of circuit blocks; and

a condenser chip having a plurality of condensers,

wherein said condenser chip is stacked on said semiconductor chip, and

wherein said plurality of condensers are provided corresponding to the respective circuit blocks and each of said plurality of condensers connects said power supply line and said ground line to function as a noise reduction condenser.

Claim 19 (new): A semiconductor device comprising:

a semiconductor chip having a plurality of circuit blocks, a power supply line and a ground line, said power supply line and said ground line being connected to each of said plurality of circuit blocks; and

a plurality of condenser chips, each of which has a condenser,

wherein said condenser chip is stacked on said semiconductor chip, and

wherein said plurality of condensers are provided corresponding to the respective circuit blocks and each of the condensers of said plurality of condenser chip connects said power supply line and said ground line to function as a noise reduction condenser.

Claim 20 (new): A semiconductor device comprising:

a semiconductor chip having a circuit block, a power supply line and a ground line, said power supply line and said ground line being connected to said circuit block; and

a condenser chip having a condenser,

wherein said condenser chip is stacked on said semiconductor chip, and

wherein said semiconductor chip has a first electrode pad provided on a connecting line which connects said circuit block and one of said power supply line and said ground line, and said condenser chip has a second electrode pad connected to said condenser; and

wherein said first electrode pad is electrically connected to said second electrode pad through a bonding wire so that said condenser function as a noise reduction condenser.

Claim 21 (new): A semiconductor device comprising:

a semiconductor chip having a circuit block, a power supply line and a ground line, said power supply line and said ground line being connected to said circuit block; and

a condenser chip having a condenser,

wherein said condenser chip is stacked on said semiconductor chip,

wherein said semiconductor chip has a first electrode pad provided on a connecting line which connects said circuit block and one of said power supply line and said ground line, and said condenser chip has a second electrode pad connected to said condenser; and

wherein said first electrode pad is electrically connected to said second electrode pad by flip chip bonding so that said condenser functions as a noise reduction condenser.

Claim 22 (new): The semiconductor device as claimed in claim 20,
wherein said semiconductor chip has a third electrode pad other than said first electrode
pad connected to said circuit block, said third electrode pad being separated from said circuit
block;

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said condenser chip has a fourth electrode pad other than said second electrode pad
connected to said condenser, said fourth electrode pad being separated from said condenser; and
an inductor is formed by connecting said third electrode pad, said fourth electrode pad and
one of said power line and said ground line through a bonding wire to function as a noise
reduction inductor.

Claim 23 (new): The semiconductor device as claimed in claim 22,
wherein a plurality of said third electrode pads are provided for said semiconductor chip
and a plurality of said fourth electrode pads are provided for said condenser chip; and
said inductor is formed by alternately and sequentially connecting said third electrode pads
and said fourth electrode pads through bonding wires.

Claim 24 (new): A semiconductor device as claimed in claim 18,
wherein said power supply line and said ground line each have a ring shaped configuration,
said plurality of circuit blocks are formed inside said ring shaped power supply line and
ground line, and

each of said plurality of condensers is connected to the corresponding circuit block through an electrode pad provided on a connecting line which connects the corresponding circuit block and one of said ring shaped power supply line and ground line.

Claim 25 (new): The semiconductor device as claimed in claim 19,
wherein said power supply line and said ground line have a ring shaped configuration,
said plurality of circuit blocks are formed inside said ring shaped power supply line and said ground line, and

each of the condensers is connected to the corresponding circuit block through an electrode pad provided on a connecting line which connects the corresponding circuit block and one of said ring shaped power supply line and ground line.

Claim 26 (new): The semiconductor device as claimed in claim 20,
wherein said semiconductor chip has a third second electrode pad other than said first electrode pad connected to said circuit block, said third electrode pad being separated from said circuit block;

said condenser chip has a fourth electrode pad other than said second electrode pad connected to the condenser, said fourth electrode pad being separated from said condenser; and

an inductor is formed by connecting said third electrode pad, said fourth electrode pad and one of said power supply line and said ground line through a bonding wire to function as a noise reduction inductor.

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Claim 27 (new): The semiconductor device as claimed in claim 26,
wherein a plurality of said third electrode pads are provided for said semiconductor chip
and a plurality of said fourth electrode pads are provided for said condenser chip; and
said inductor is formed by alternately and sequentially connecting said third electrode pads
and said fourth electrode pads through bonding wires.
